

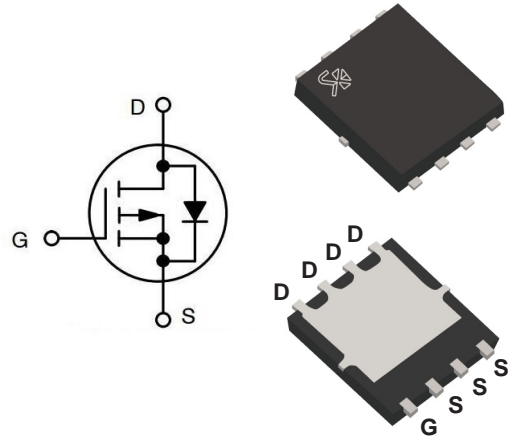
100V P-Channel MOSFET

Feature

- 100 V P-Channel MOSFET High Dense Design.
- Ultra low On-Resistance.
- Reliable and Rugged.

Applications

- Power Management in Notebook Computer, and Portable Equipment and Battery Systems.



PDFN5060

Maximum Ratings (TC=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-100V	V
Gate-Source Voltage	V _{GSS}	±20V	V
Drain Current-Continuous @ TC=25°C	I _D	-5	A
Drain Current-Pulsed	I _{DM}	-20	A
Operating Junction Temperature Range	T _J	-50 to 150°C	°C

Electrical Characteristics (TA=25°C unless otherwise noted)

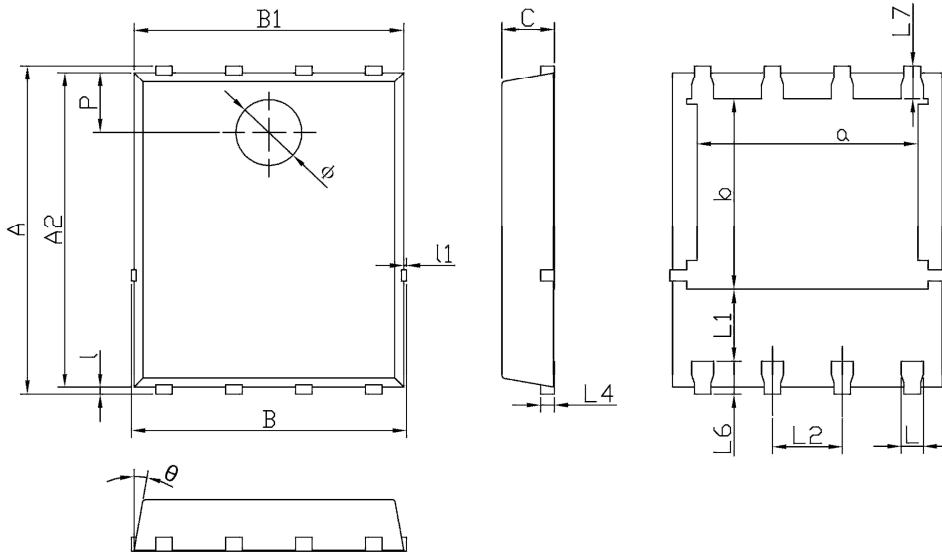
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTIC						
Drain-Source Breakdown Voltage	B _{VDSS}	V _{GS} =0V, I _D =-250uA	-100	-	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-80V, V _{GS} =0V, T _J =25°C	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
ON CHARACTERISTIC						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-	-2.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-5A	-	170	210	mΩ
		V _{GS} =-4.5V, I _D =-2A	-	190	220	
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-1A	-	-0.75	-	V

NOTE:

1. The data tested by pulsed, pulse with ≤ 300us, duty cycle ≤ 2%.
2. R_{dson} calculated by - package type.

PDFN5060

Unit:mm



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	5.90	6.00	6.10
a	3.91	4.01	4.11
A2	5.70	5.75	5.80
B	4.90	5.00	5.10
b	3.37	3.47	3.57
B1	4.80	4.90	5.00
C	0.90	0.95	1.00
L	0.35	0.40	0.45
l	0.06	0.13	0.20
L1	1.10	-	-
l1	-	-	0.10
L2	1.17	1.27	1.37
L4	0.21	0.26	0.34
L6	0.51	0.61	0.71
L7	0.51	0.61	0.71
P	1.00	1.10	1.20
θ	8°	10°	12°
ϕ	1.10	1.20	1.30